

Sollentuna, Sweden

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## Summary:

Bo finished his education, Applied Engineering ( Teknisk fysik ) at the Institute of Technology Stockholm, KTH, 1982.

He started his first employment at the Swedish Institute of Microwave Technology, SIMT, 1982 as a scientist in compound semiconductor development for materials and devices.

Soon Bo got responsibility to start up Hydride Vapor Phase Epitaxy of InGaAsP from scratch. Meanwhile InGaAsP material characterizations was designed , rebuilt and set up such as PL, DCX-Ray, Hall measurements and IV in Bo's small group

Bo was 1983 offered a 12 months position at Bell Labs Murray Hill NJ, US in their team to develop and improve HVPE for InGaAsP. Here he also discovered a new way to make semi-insulating InP:Fe by HVPE and nitrogen as a carrier gas. After Bell labs he joined Epitaxx, Princeton spin out from RCA, for 6 months. His group started development of a Superluminescent 1,3 um LED for fiberoptic communication.

After this a brand new very much improved HVPE system was designed and built at the SIMT, and very good InGaAsP could be epitaxially grown and characterized. Also High Speed ( 20+ GHz) laserdiodes was regrown with HVPE InP:Fe material.

1987 Bo started a Ph D program ... which he discontinued 1990 when he got a job in the industry.

1990 Bo changed direction into Sales and Marketing of high end devices for Fiberoptic ( 2,4 + 10 Gbps Laserdiodes and detectors) , RF&MW devices ( HEMTs). Customer focus was Ericsson ( I was Global Account Manager) and Nokia.

During 1990 to 2002 I spent years with Lucent Microelectronics , startups: Multiplex Inc NJ US ( spinout from Bell Labs) and WaveSplitter Technologies CA, US.

2005 Bo started his new role as a Swedish Innovator and together with prof Mikael Östling and Martin Domeij Ph D from KTH TranSiC.

TranSiC and Scint-X was part of STING the Stockholm Incubator's program.

Next:

1. TranSiC 2005 – Electrum SiC 1200 V Power Transistor
2. Scint-X 2006 – Electrum Scintillator for HD X-ray
3. SenSiC 2007 – LiU , Chalmers and Electrum SiC for high temp sensors: CO<sub>2</sub>,NH<sub>3</sub> & NO<sub>x</sub>.
4. Epiclarus – 2009 , Electrum InP on Si for Photonic Integrated Circuits
5. Nocilis Materials 2010 Electrum SiGeSn and GeSn on Si
6. Ascatron 2011 Electrum SiC medium voltage ( 10 kV ) SiC diodes and MOS-transistors.
7. Epiluvac 2013 in the C3NiT program LiU WBG Epitaxy equipment.

Also I am/was a MOB in

1. KISABSEmi , Kista
2. C3NiT, LiU
3. NanoSized, Uppsala-Kista
4. SenSiC

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